

International Application No.: PCT/JP2004/018605
U.S. Patent Application No.: Unknown
June 16, 2006
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IN THE ABSTRACT:

Please replace the Abstract of the Disclosure originally filed with the above-identified patent application with the following new Abstract of the Disclosure:

ABSTRACT OF THE DISCLOSURE

A nonvolatile memory device improves the accuracy of screening testing while applying a voltage at or lower than the limit of the withstand voltage of an element for high voltage in the screening testing. The nonvolatile memory device includes a high voltage production circuit that produces a high voltage, a high voltage waveform conversion circuit to which the high voltage is input and which converts the voltage waveform, and a memory cell section provided with memory cells in which data rewriting is performed as a result of applying the converted high voltage. The high voltage waveform conversion circuit includes a test signal input section TEST and applies the high voltage input from the high voltage production circuit to the memory cell section without converting the voltage waveform when a test signal is input to the test signal input section.